

SCHOTTKY DIE SPECIFICATION

TYPE: SB10100

General Description: 100 V 10 A Standard VF

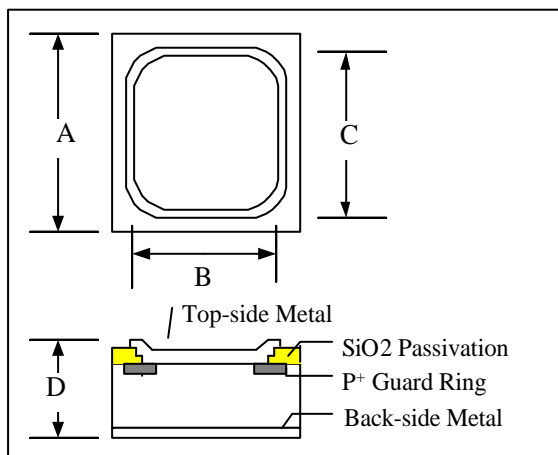
Single Anode

ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage: $I_r=1\text{mA}$ (for wafer form)	VRRM	100	105	Volt
$I_r=0.5\text{mA}$ (for dice form)				
Average Rectified Forward Current	IFAV	10		Amp
Maximum Instantaneous Forward Voltage				
@ 10 Amperes, $T_a=25^\circ\text{C}$	VF MAX	0.83	0.82	Volt
Maximum Instantaneous Reverse Voltage				
$V_R=100$ Volt, $T_a=25^\circ\text{C}$	IR MAX	0.2	0.18	mA
Maximum Junction Capacitance @ 0V, 1MHZ	Cj MAX			pF
MAXIMUM RATINGS				
Nonrepetitive Peak Surge Current	IFSM	200		Amp
Operating Junction Temperature	Tj	-65 to +125		$^\circ\text{C}$
Storage Temperatures	TSTG	-65 to +125		$^\circ\text{C}$

Specification apply to die only. Actual performance may degrade when assembled.

MEMT does not guarantee device performance after assembly.

Data sheet information is subjected to change without notice.

DICE OUTLINE DRAWING


DIM	ITEM	μm^2	Mil ²
A	Die Size	2590	101.97
B	Top Metal Pad Size	2490	98.0
C	Passivation Seal	2510	98.8
D	Thickness (Min)	254	10
	Thickness (Max)	305	12

PS:

(1)Cutting street width is around 80 μm (3.14mil).

(2)Both of top-side and back-side metals are Ti/Ni/Ag.